



XTR1N0800

High Temperature 80V Diode Family

Rev 3 – August 2021 (DS-00131-11)

Data Sheet



PRODUCTION



DIP8
XTR1N0815
XTR1N0850



FEATURES

- Reverse voltage $V_R > 90V$.
- Operational beyond the $-60^{\circ}C$ to $+230^{\circ}C$ temperature range.
- Forward current @ $230^{\circ}C$, $V_F=1.2V$:
 - XTR1N0815: $I_F=216mA$ per diode.
 - XTR1N0850: $I_F=660mA$ per diode.
- Forward voltage @ $85^{\circ}C$, $I_F=1mA$:
 - XTR1N0815: $V_F=640mV$ per diode.
 - XTR1N0850: $V_F=600mV$ per diode.
- Ruggedized SMT and thru-hole packages.
- Also available as bare die.

APPLICATIONS

- Reliability-critical, Automotive, Aeronautics & Aerospace, Down-hole.
- General rectification, voltage blocking and clamping, power supplies.

DESCRIPTION

XTR1N0800 is a family of general-purpose diodes with a reverse voltage above 90V. Each part is composed of four independent diodes which can be used individually, in half- or full-bridge rectifier architecture or connected in series or parallel.

Typical applications include rectification, demodulation, voltage blocking, voltage clamping, power supplies, charge pumps and voltage multipliers.

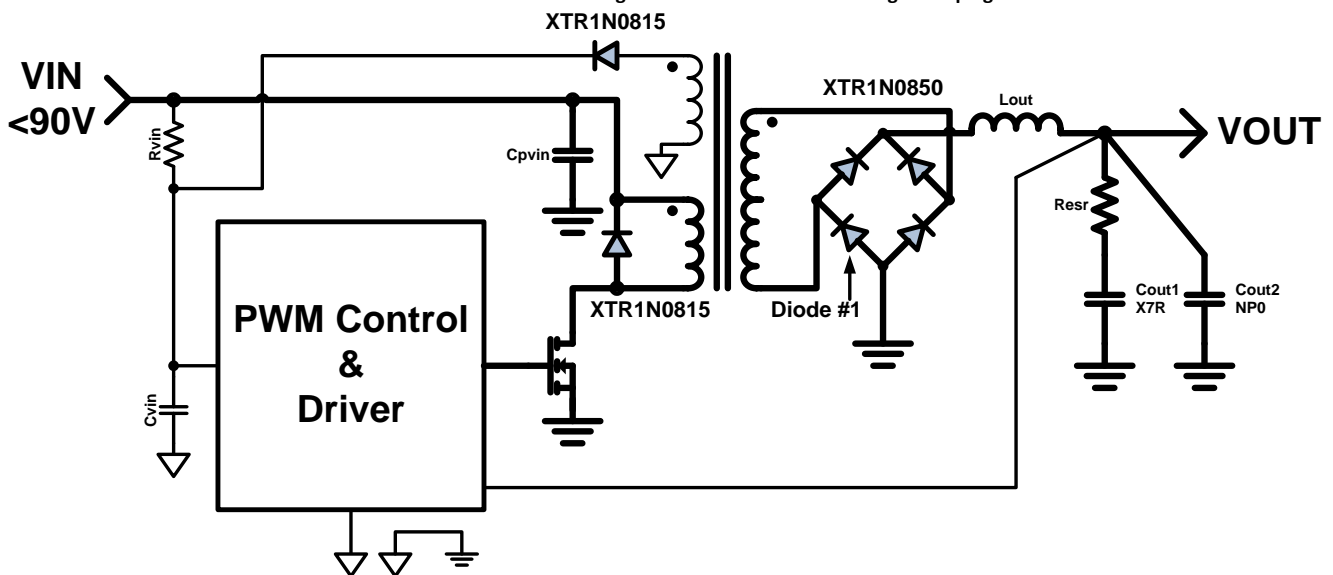
Full functionality is guaranteed from $-60^{\circ}C$ to $+230^{\circ}C$, though operation well below and above this temperature range is achieved.

XTR1N0800 parts have been designed to reduce system cost and ease adoption by reducing the learning curve and providing easy to use features.

Parts from the XTR1N0800 family are available in ruggedized SMT and thru-hole packages. Parts are also available as bare dies.

PRODUCT HIGHLIGHT

Diodes used in half- and full-bridge rectification as well as voltage clamping



ORDERING INFORMATION

X
↓
Source :
X = X-REL Semi

TR
↓
Process:
TR = HiTemp, HiRel

1N
↓
Part family

08xx
↓
Part number

Product Reference	Temperature Range	Package	Pin Count	Marking
XTR1N0815-TD	-60°C to +230°C	Tested Bare Die		
XTR1N0815-D	-60°C to +230°C	Ceramic side braze DIP	8	XTR1N0815
XTR1N0850-TD	-60°C to +230°C	Tested Bare Die		
XTR1N0850-D	-60°C to +230°C	Ceramic side braze DIP	8	XTR1N0850

Other packages and packaging configurations possible upon request. For some packages or packaging configurations, MOQ may apply.

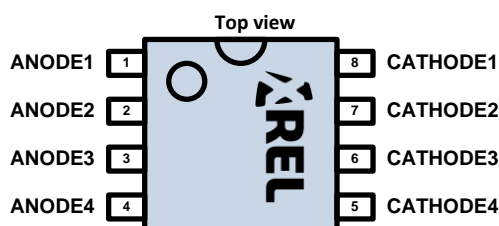
ABSOLUTE MAXIMUM RATINGS

Repetitive peak reverse voltage V_{RRM}	90V
Continuous peak reverse voltage V_R	90V
Continuous forward current I_F @230°C	
XTR1N0815	0.5A
XTR1N0850	1.6A
Operating Junction Temperature Range	-70°C to +300°C

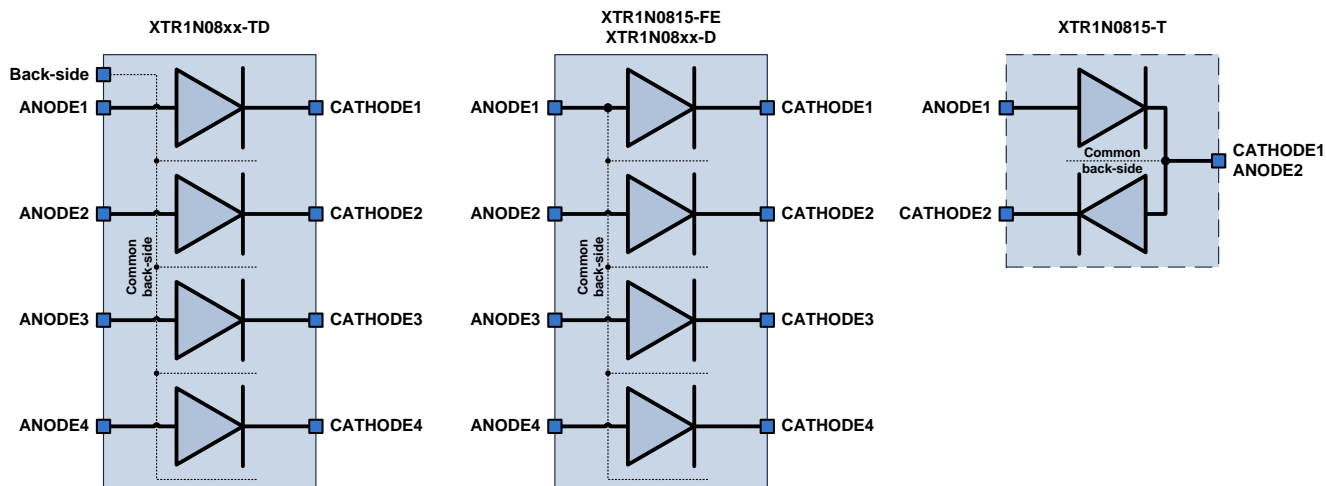
Caution: Stresses beyond those listed in "ABSOLUTE MAXIMUM RATINGS" may cause permanent damage to the device. These are stress ratings only and functionality of the device at these or any other condition beyond those indicated in the operational sections of the specifications is not implied. Exposure to "ABSOLUTE MAXIMUM RATINGS" conditions for extended periods may permanently affect device reliability.

PACKAGING OPTIONS

Side Brazed DIP8
XTR1N08XX-D



BLOCK DIAGRAM



Important Notices:

Dashed lines indicate the back-side connection for the different packages.

For best reverse voltage performance, the back-side must be connected to the most negative voltage seen by the diodes.

In case a diode is not used, the diode should be shorted and tied to a fixed voltage in the application or at least to a terminal of any active diode.

THERMAL CHARACTERISTICS

Parameter	Condition	Min	Typ	Max	Units
XTR1N08XX-D (DIP8)					
Thermal Resistance: J-C R_{Th_J-C}			20		°C/W
Thermal Resistance: J-A R_{Th_J-A}	Still air.		100		°C/W

RECOMMENDED OPERATING CONDITIONS

Parameter	Min	Typ	Max	Units
Reverse voltage V_R			80	V
Forward voltage V_F			1.5	V
Continuous forward current per diode @ T _j =25°C I_F XTR1N0815 XTR1N0850		0.34 1.10		A
Junction Temperature ¹ T_j	-60		230	°C

¹ Operation beyond the specified temperature range is achieved.

XTR1N0815 ELECTRICAL SPECIFICATIONS

Unless otherwise stated, specification applies for one diode and $-60^{\circ}\text{C} < T_j < 230^{\circ}\text{C}$.

Parameter	Condition	Min	Typ	Max	Units
Electrical Characteristics					
Forward Voltage V_F	$I_F=1\text{mA}$ $T_C=-60^{\circ}\text{C}$ $T_C=85^{\circ}\text{C}$ $T_C=230^{\circ}\text{C}$		860 640 460		mV
Forward Current I_F	$V_F=1.2\text{V}$ $T_C=-60^{\circ}\text{C}$ $T_C=85^{\circ}\text{C}$ $T_C=230^{\circ}\text{C}$		152 195 216		mA
Reverse Current I_R	$V_R=80\text{V}$ $T_C=-60^{\circ}\text{C}$ $T_C=85^{\circ}\text{C}$ $T_C=230^{\circ}\text{C}$		<0.001 0.005 3.5		μA
Switching Characteristics					
Diode Capacitance C_d	$F=200\text{KHz}$, $V_R=0\text{V}$, $T_C=230^{\circ}\text{C}$ $F=200\text{KHz}$, $V_R=60\text{V}$, $T_C=230^{\circ}\text{C}$		51 14		pF
Reverse Recovery Time t_{rr1}	$I_F = I_{rm} = 100\text{ mA}$, t_{rr} at 25% of I_{rm} $T_C=-60^{\circ}\text{C}$ $T_C=85^{\circ}\text{C}$ $T_C=230^{\circ}\text{C}$		22 39 51		ns
Reverse Recovery Time t_{rr2}	$I_F = 100\text{ mA}$, $V_R = -6\text{V}$, t_{rr} at 25% of I_{rm} $T_C=-60^{\circ}\text{C}$ $T_C=85^{\circ}\text{C}$ $T_C=230^{\circ}\text{C}$		31 50 66		ns

XTR1N0850 ELECTRICAL SPECIFICATIONS

Unless otherwise stated, specification applies for one diode and $-60^{\circ}\text{C} < T_j < 230^{\circ}\text{C}$.

Parameter	Condition	Min	Typ	Max	Units
Electrical Characteristics					
Forward Voltage V_F	$I_F=1\text{mA}$ $T_C=-60^{\circ}\text{C}$ $T_C=85^{\circ}\text{C}$ $T_C=230^{\circ}\text{C}$		845 600 335		mV
Forward Current I_F	$V_F=1.2\text{V}$ $T_C=-60^{\circ}\text{C}$ $T_C=85^{\circ}\text{C}$ $T_C=230^{\circ}\text{C}$		480 600 660		mA
Reverse Current I_R	$V_R=80\text{V}$ $T_C=-60^{\circ}\text{C}$ $T_C=85^{\circ}\text{C}$ $T_C=230^{\circ}\text{C}$		<0.002 0.02 20		μA
Switching Characteristics					
Diode Capacitance C_d	$F=200\text{KHz}$, $V_R=0\text{V}$, $T_C=230^{\circ}\text{C}$ $F=200\text{KHz}$, $V_R=60\text{V}$, $T_C=230^{\circ}\text{C}$		205 50		pF
Reverse Recovery Time t_{rr1}	$I_F = I_{rm} = 100\text{ mA}$, t_{rr} at 25% of I_{rm} $T_C=-60^{\circ}\text{C}$ $T_C=85^{\circ}\text{C}$ $T_C=230^{\circ}\text{C}$		40 61 72		ns
Reverse Recovery Time t_{rr2}	$I_F = 100\text{ mA}$, $V_R = -6\text{V}$, t_{rr} at 25% of I_{rm} $T_C=-60^{\circ}\text{C}$ $T_C=85^{\circ}\text{C}$ $T_C=230^{\circ}\text{C}$		42 67 83		ns

XTR1N0815 TYPICAL PERFORMANCE

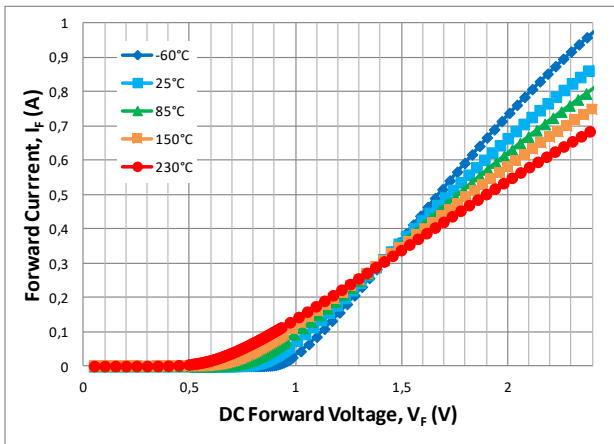


Figure 1. Forward current (I_F) vs DC forward voltage (V_F) for several case temperatures. Linear vertical axis.

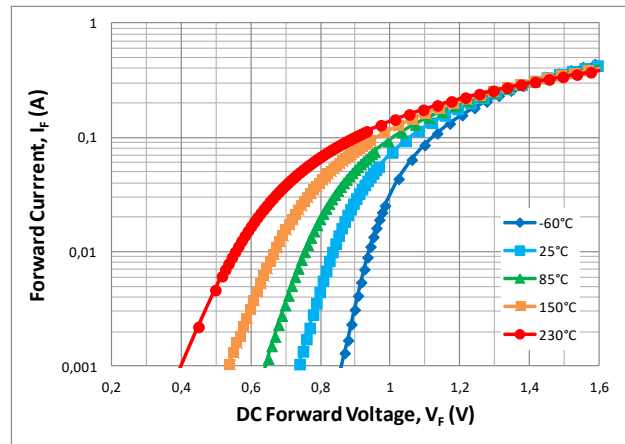


Figure 2. Forward current (I_F) vs DC forward voltage (V_F) for several case temperatures. Logarithmic vertical axis.

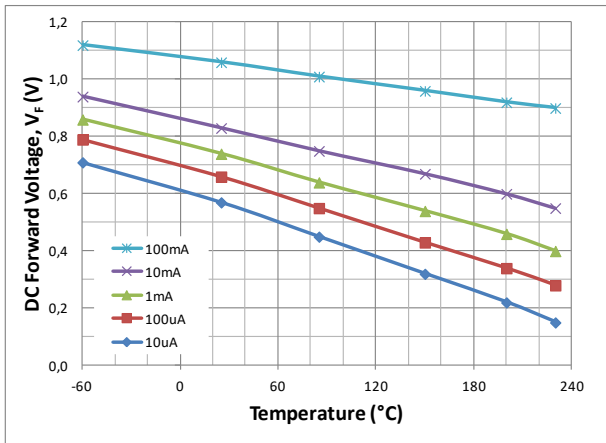


Figure 3. DC forward voltage (V_F) vs case temperature for several forward currents (I_F).

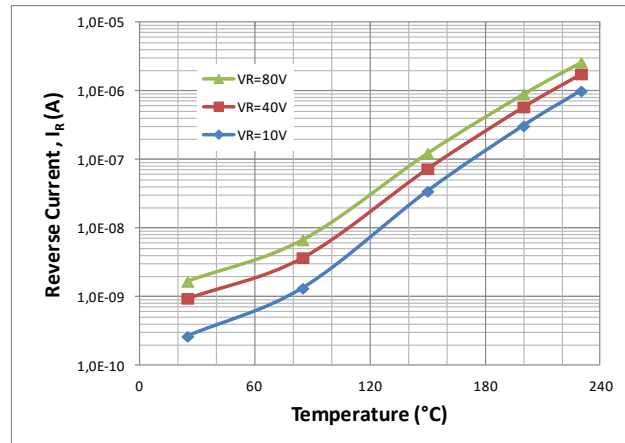


Figure 4. Reverse current (I_R) vs case temperature for several reverse voltages (V_R).

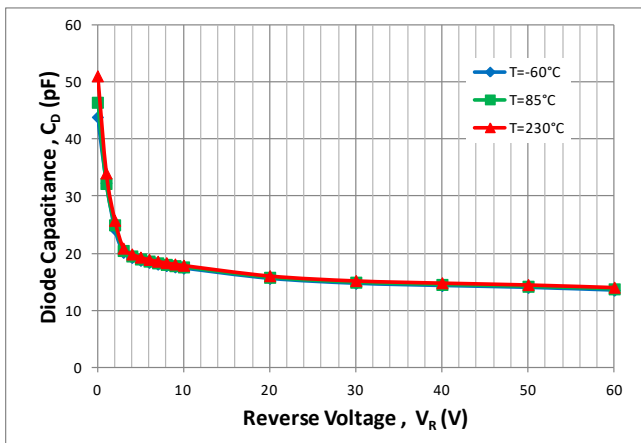


Figure 5. Diode capacitance (C_D) vs reverse voltage (V_R) for several case temperatures (I_F) with $F=200\text{KHz}$.

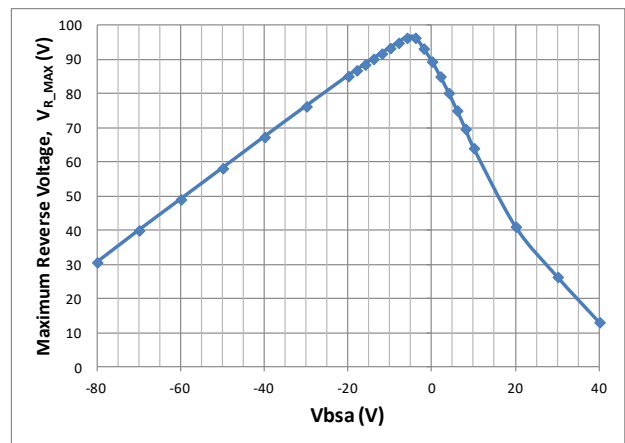


Figure 6. Maximum allowed reverse voltage (V_{R_MAX}) vs back-side to anode voltage (see Block Diagram in page 2). Worst case values.

XTR1N0850 TYPICAL PERFORMANCE

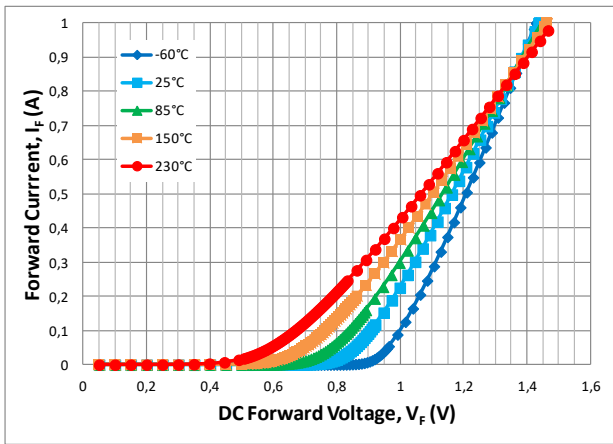


Figure 7. Forward current (I_F) vs DC forward voltage (V_F) for several case temperatures. Linear vertical axis.

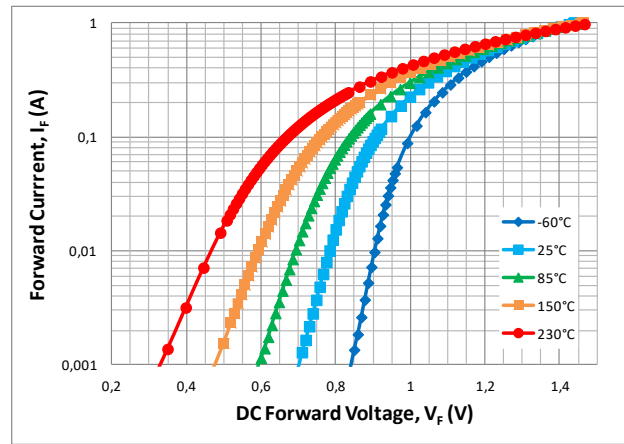


Figure 8. Forward current (I_F) vs DC forward voltage (V_F) for several case temperatures. Logarithmic vertical axis.

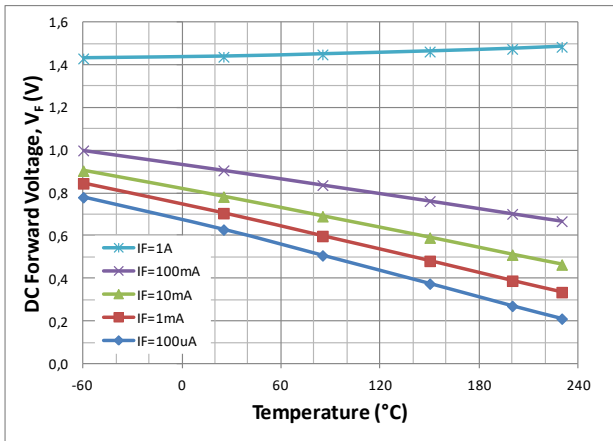


Figure 9. DC forward voltage (V_F) vs case temperature for several forward currents (I_F).

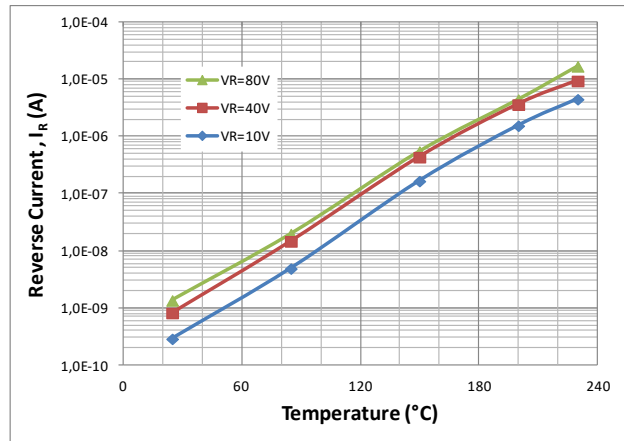


Figure 10. Reverse current (I_R) vs case temperature for several reverse voltages (V_R).

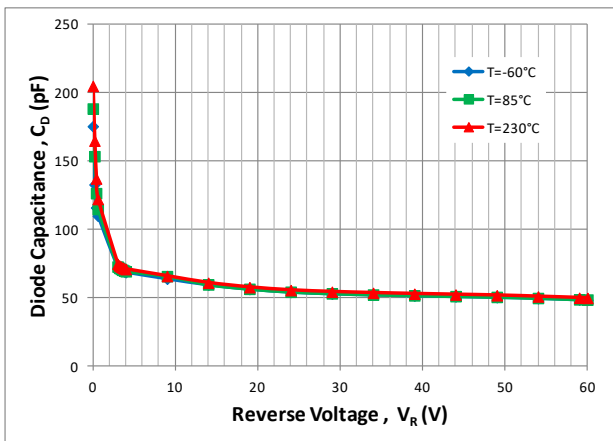


Figure 11. Diode capacitance (C_D) vs reverse voltage (V_R) for several case temperatures (I_F) with $F=200\text{KHz}$.

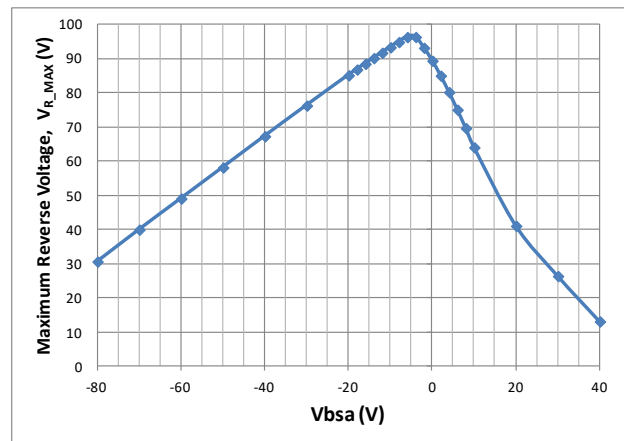


Figure 12. Maximum allowed reverse voltage (V_{R_MAX}) vs back-side to anode voltage (see Block Diagram in page 2). Worst case values.

PARAMETER DEFINITION (TRR)

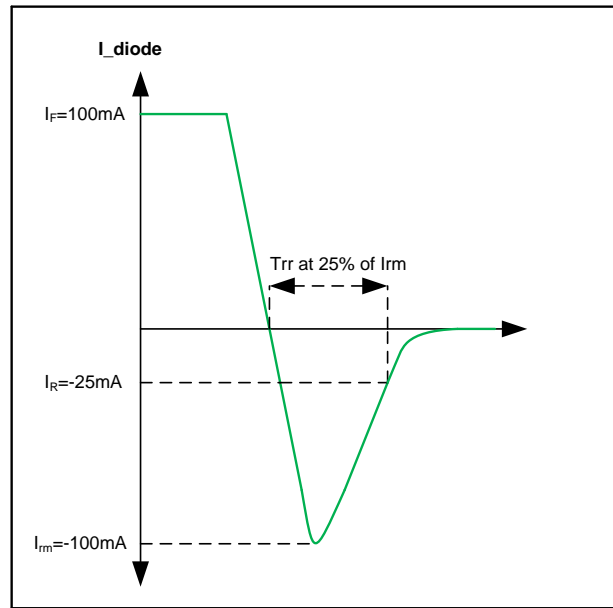


Figure 13. Reverse recovery time definition for $I_F = I_{RM} = 100\text{mA}$.

THEORY OF OPERATION

Introduction

The XTR1N0800 is a family of general-purpose diodes able to operate from -60°C to $+230^{\circ}\text{C}$ and withstand reverse voltages up to 90V.

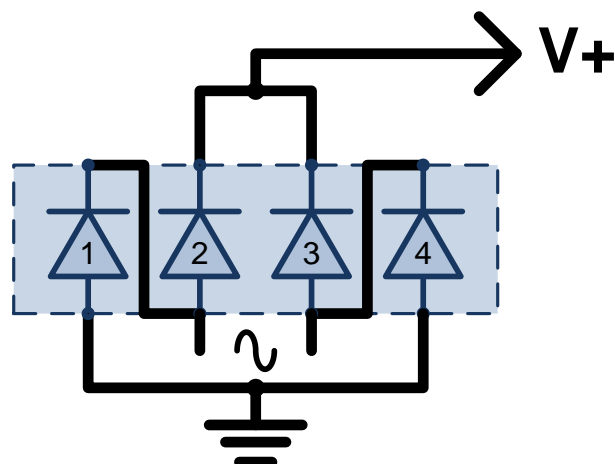
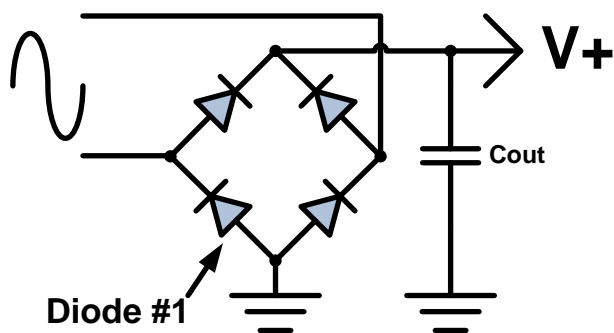
Each die is composed of four independent diodes on top of the same silicon substrate (back-side connection).

Given the construction of the diodes, the back-side voltage has an influence on the maximum allowed reverse voltage. Optimum performance is achieved for the back-side connected to the most negative voltage seen by any of the four diodes.

In TO18 packaged parts, the back-side is connected to the cathode of the first diode (CATHODE1) and the anode of the second diode (ANODE2).

In DIP8 and CDFP8 packaged parts, the back-side is connected to the anode of the first diode (ANODE1).

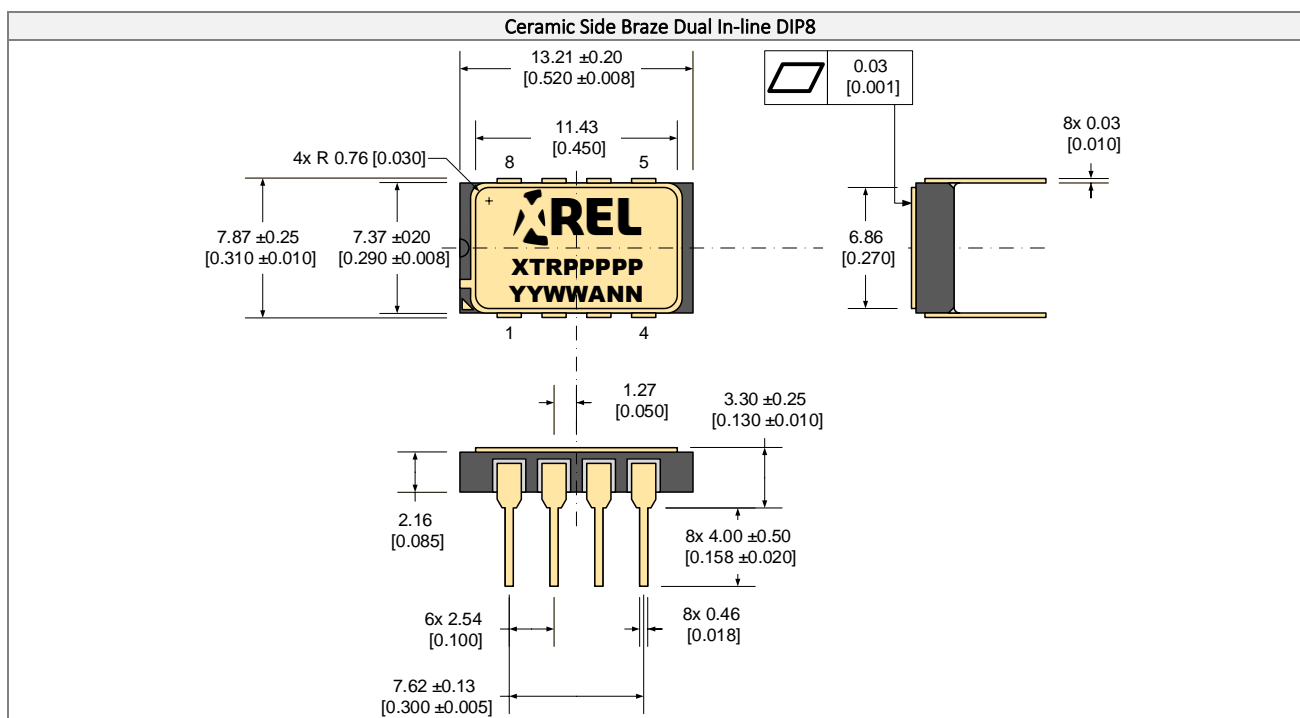
In the simple full-wave rectifier example below, if DIP8 or CDFP8 packaged versions of XTR1N0415 or XTR1N0450 are used, the optimum result in terms of reverse voltage robustness is achieved by connecting the anode of the first diode to the GND node.



The previous figure shows a simple implementation of the full-bridge rectifier at board level. Bold black lines indicate tracks on the board. In this configuration, as recommended in the previous figure, the anode of the first diode is connected to the GND node in order to offer the best reverse voltage characteristics.

PACKAGE OUTLINES

Dimensions shown in mm [inches]. Tolerance ± 0.13 mm [± 0.005 in], unless otherwise specified.



Part Marking Convention

Part Reference: XTRPPPPP	
XTR	X-REL Semiconductor, high-temperature, high-reliability product (XTRM Series).
PPPPP	Part number (0-9, A-Z).
Unique Lot Assembly Code: YYWWANN	
YY	Two last digits of assembly year (e.g. 11 = 2011).
WW	Assembly week (01 to 52).
A	Assembly location code.
NN	Assembly lot code (01 to 99).

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